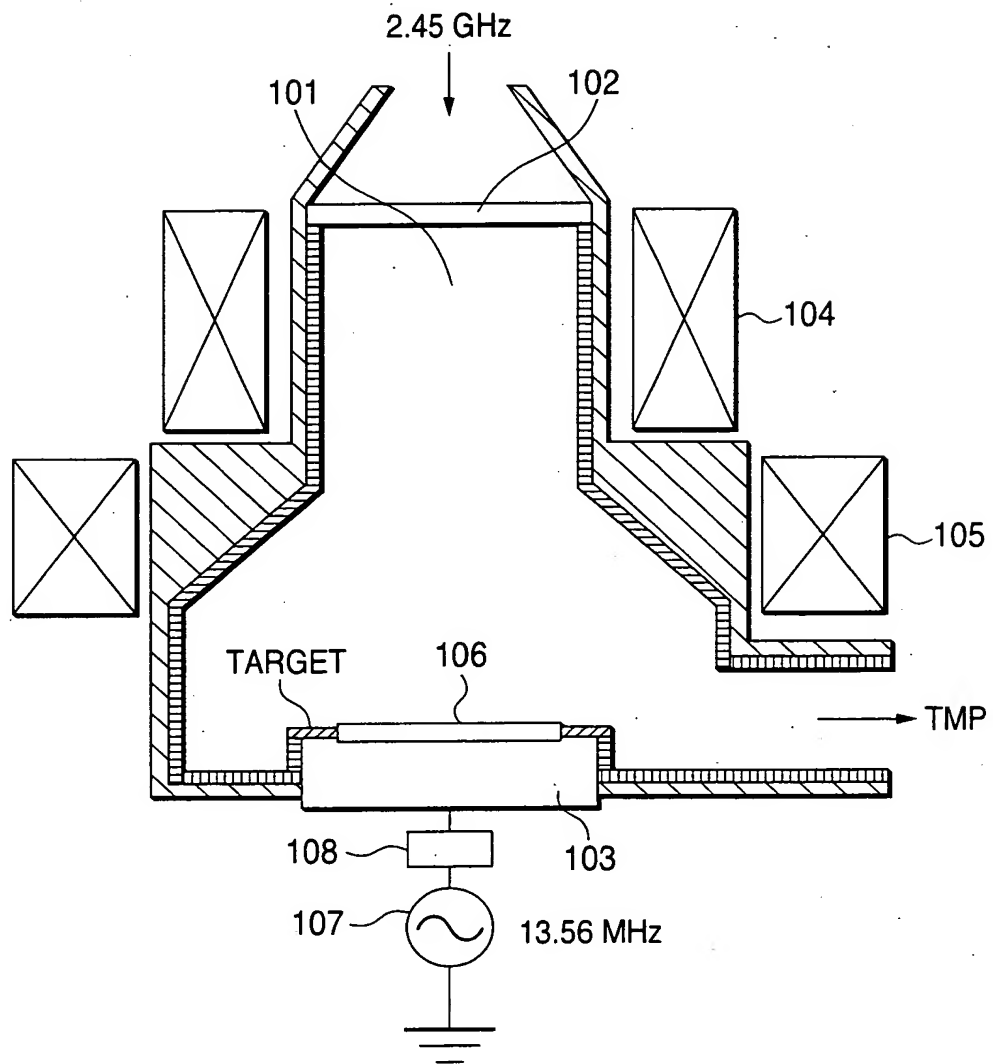


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FIG. 1





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FIG. 2A

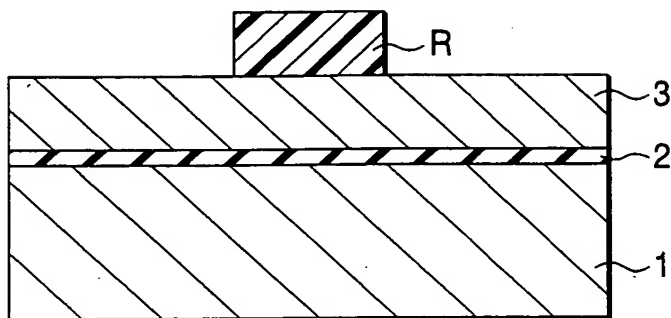


FIG. 2B

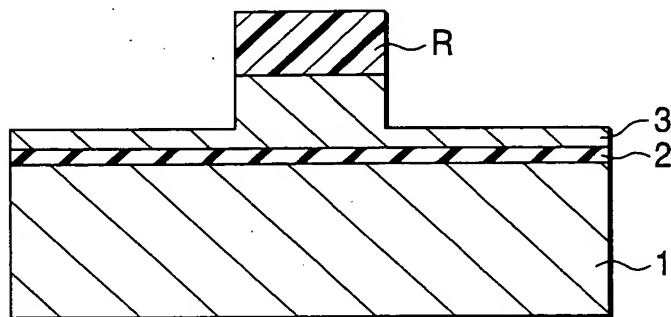
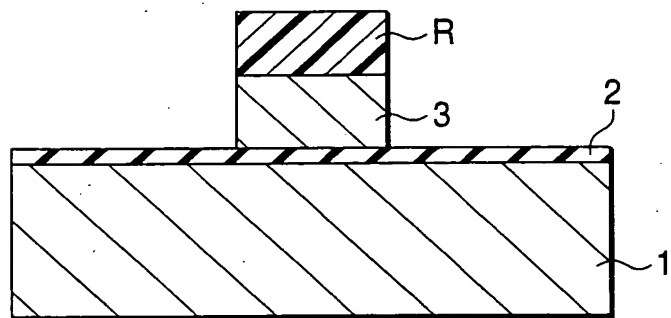


FIG. 2C



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Inventor: TABARA et al.
Docket No.: 12844.0045US01
Title: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
Serial No.: 10/682229
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FIG. 3

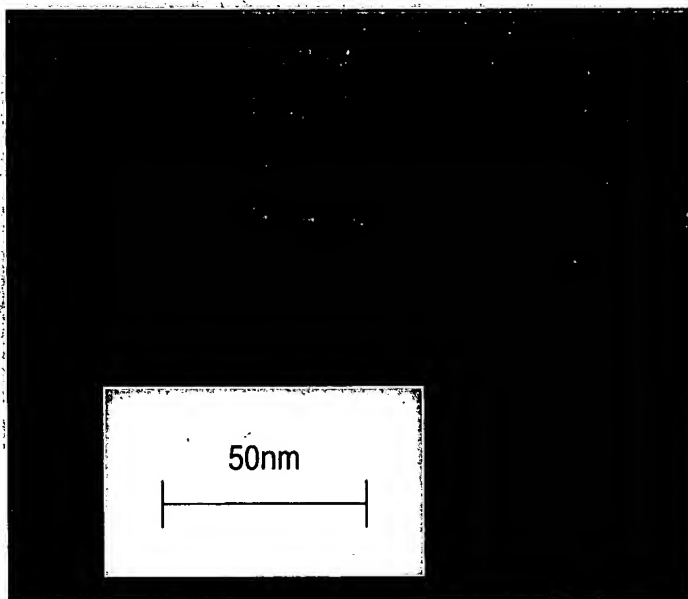
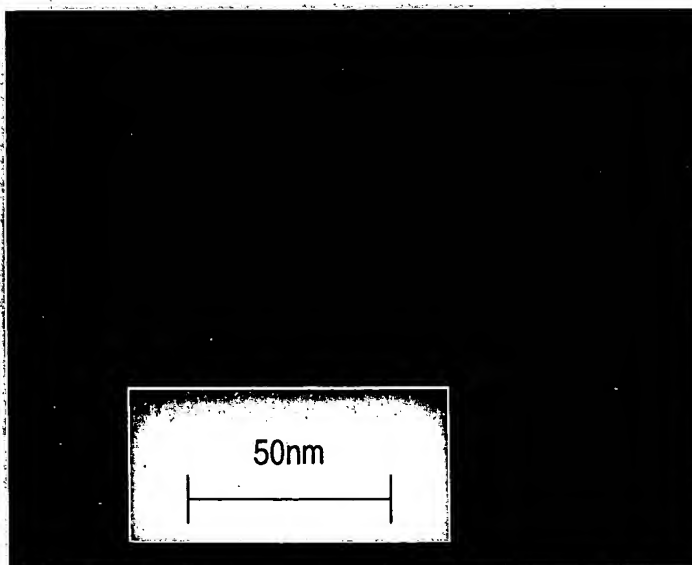


FIG. 4



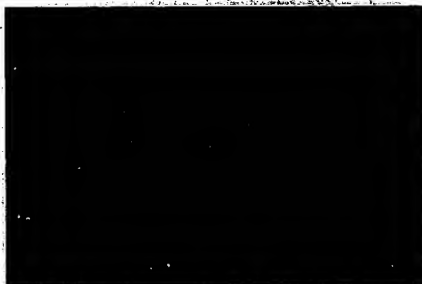


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FIG. 5



FIG. 6A



PARTIALLY ETCHED polySi

FIG. 6B



GATE OXIDE SURFACE
SURFACE MORPHOLOGY OF polySi AND GATE OXIDE

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FIG. 7

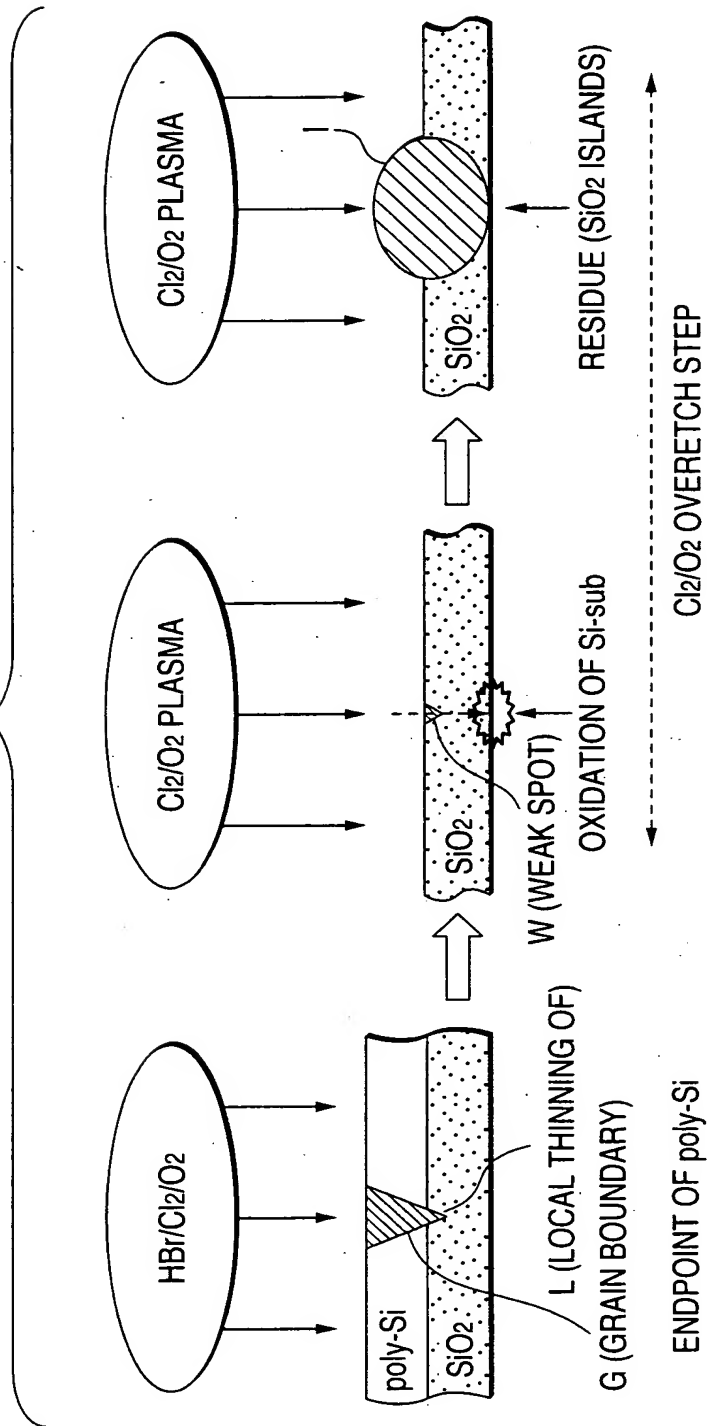




FIG. 8

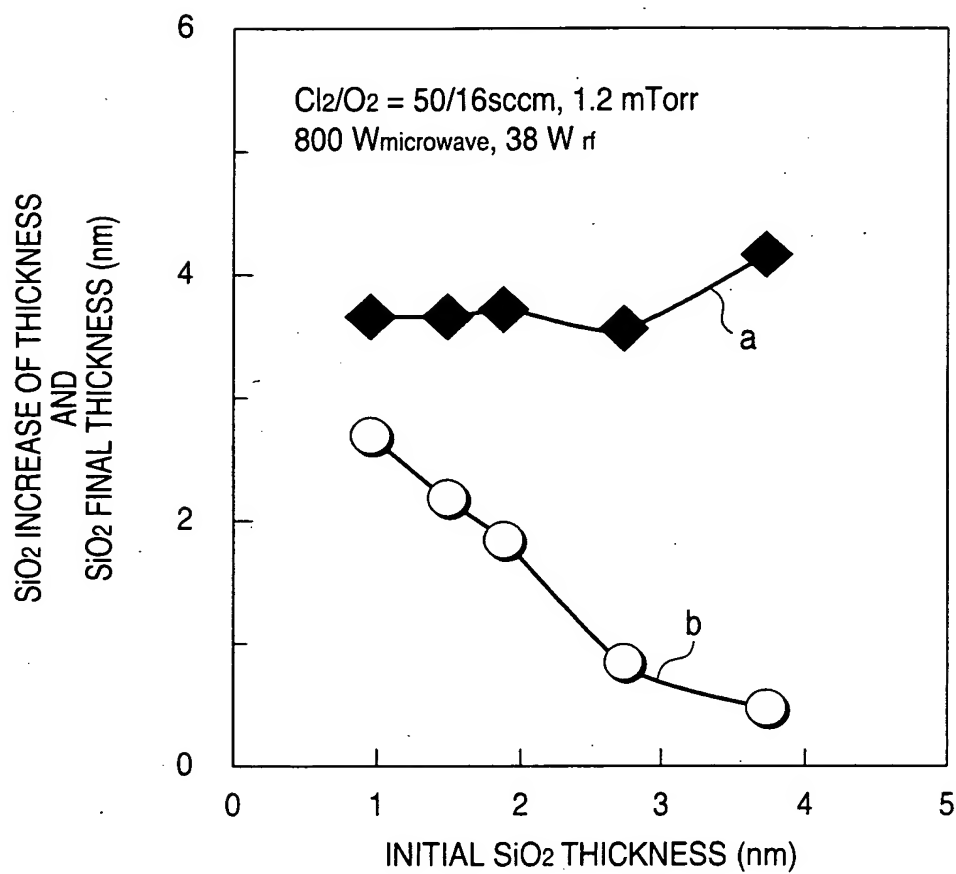




FIG. 9

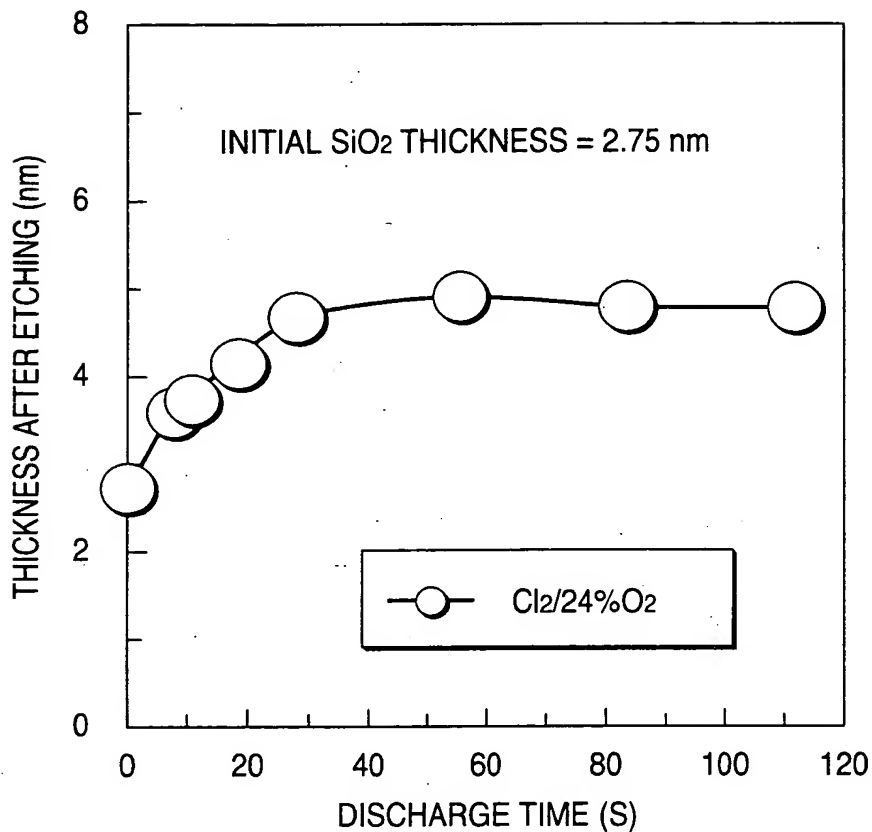


FIG. 10

